

ECE695A: Reliability Physics of Nano-Transistors Reliability Measurements

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Reliability Measurements

What is special about reliability measurements?



Precision measurements

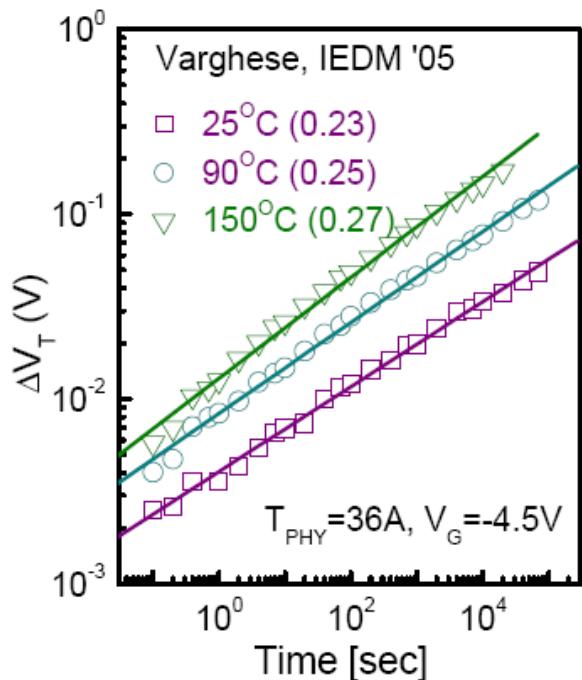
Customized measurements

Outline

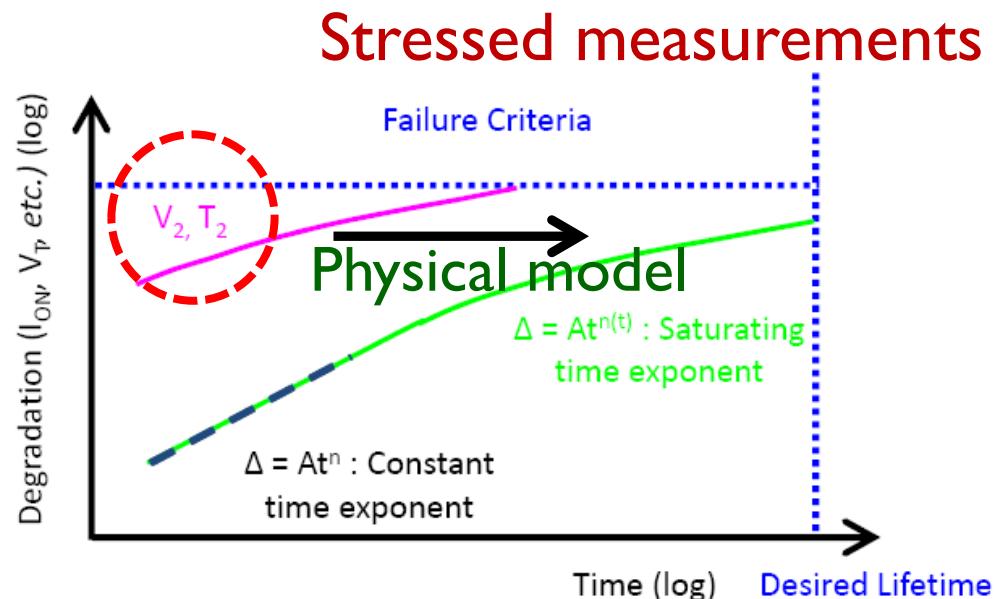
- I. Different reliability measurements**
- 2. Measurement setup
- 3. Example Codes
- 4. Data analysis
- 5. Conclusion

Different Reliability Measurements

NBTI



HCI



Measurements at low voltages/temperature can be very noisy as well as time consuming.

What should we measure

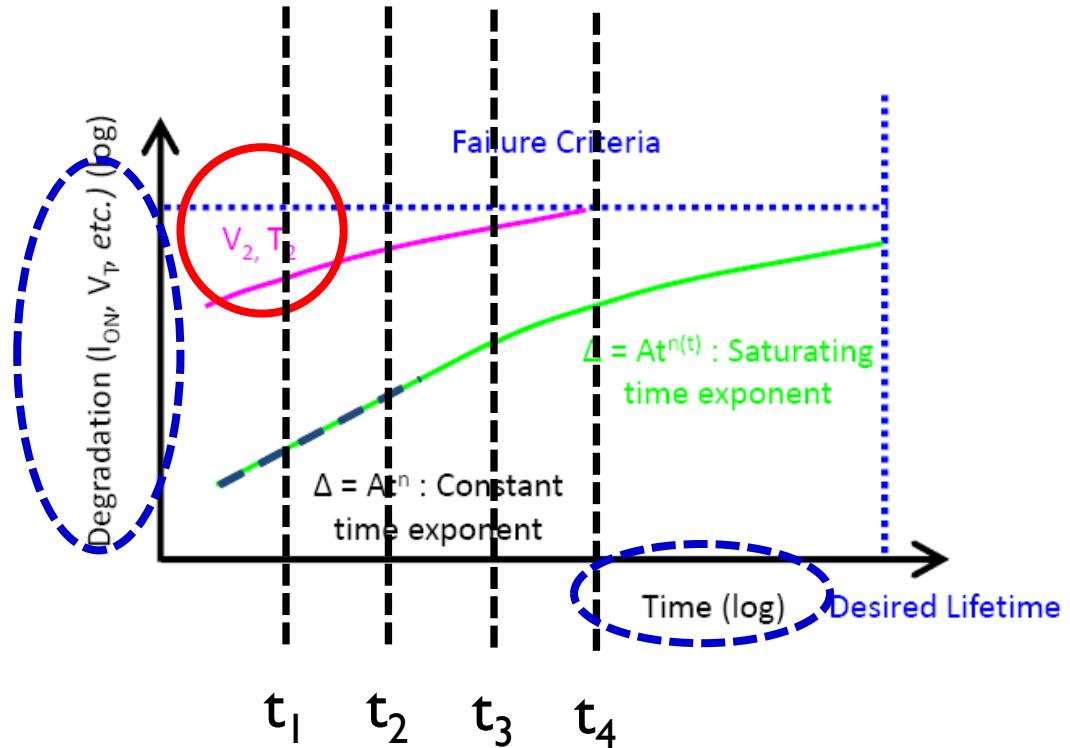
In general,

Y axis : (Some parameter that contains signature of degradation

e.g., V_T , I_G , I_D , T_{BD} ,

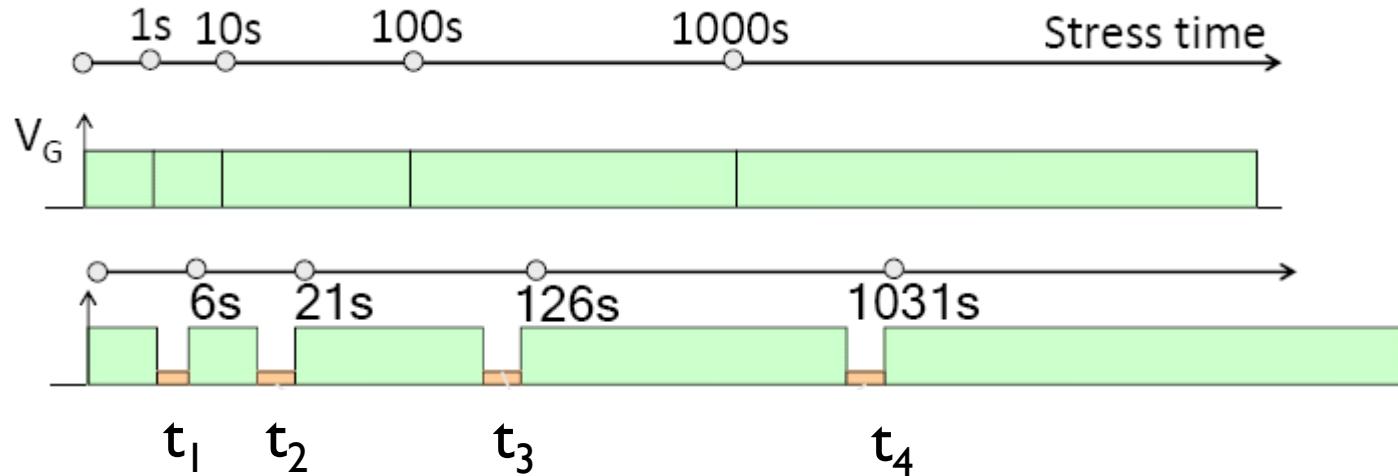
X axis: time

@ different V_{stress} , T , sample



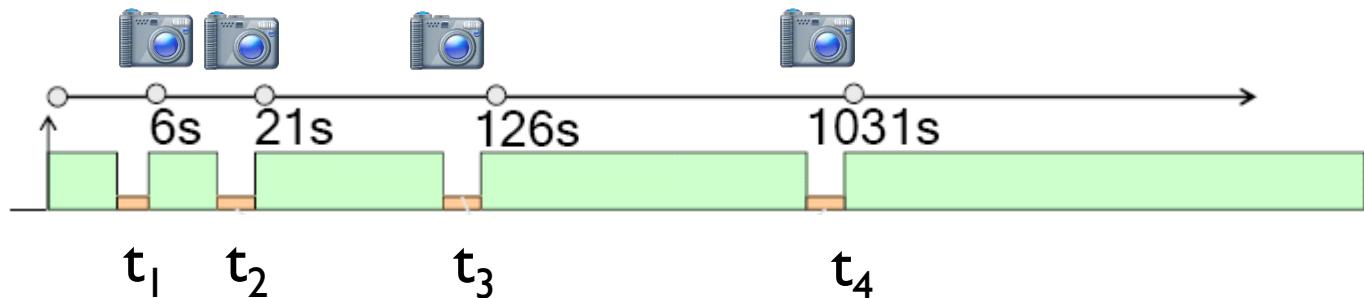
Temporal Measurement

Stressed/Temporal Measurements

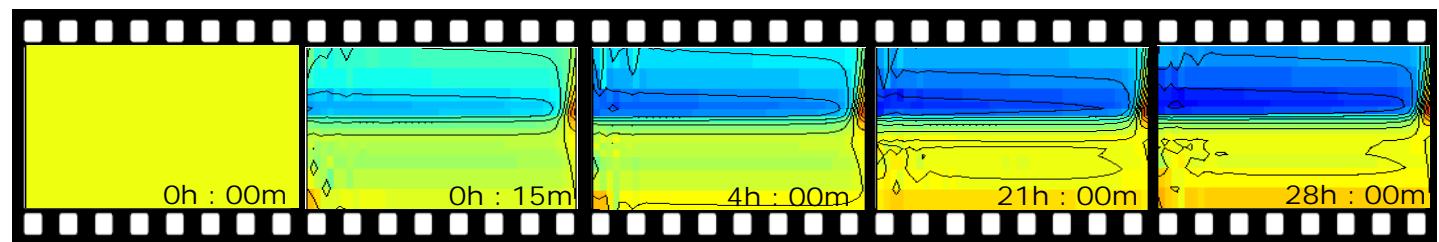


Some measurements can be done ***on the fly*** (Drain current, SILC,...)
while for some, we have to stop and measure (Id-Vg, charge pumping,...)

Measure-Stress-Measure (MSM)



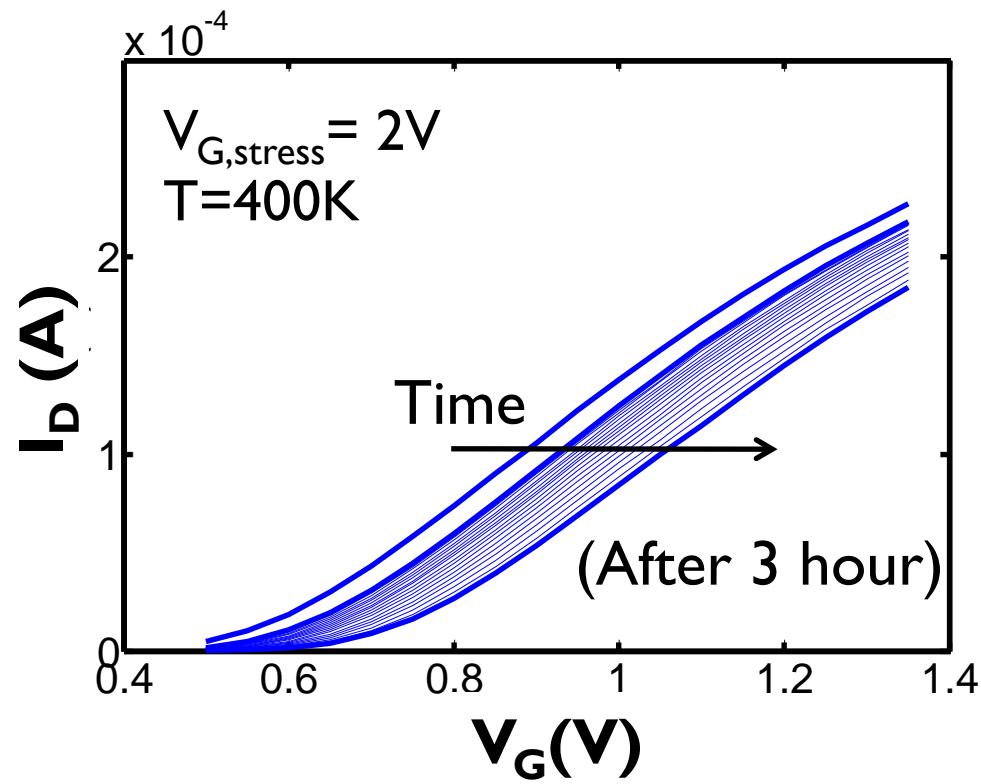
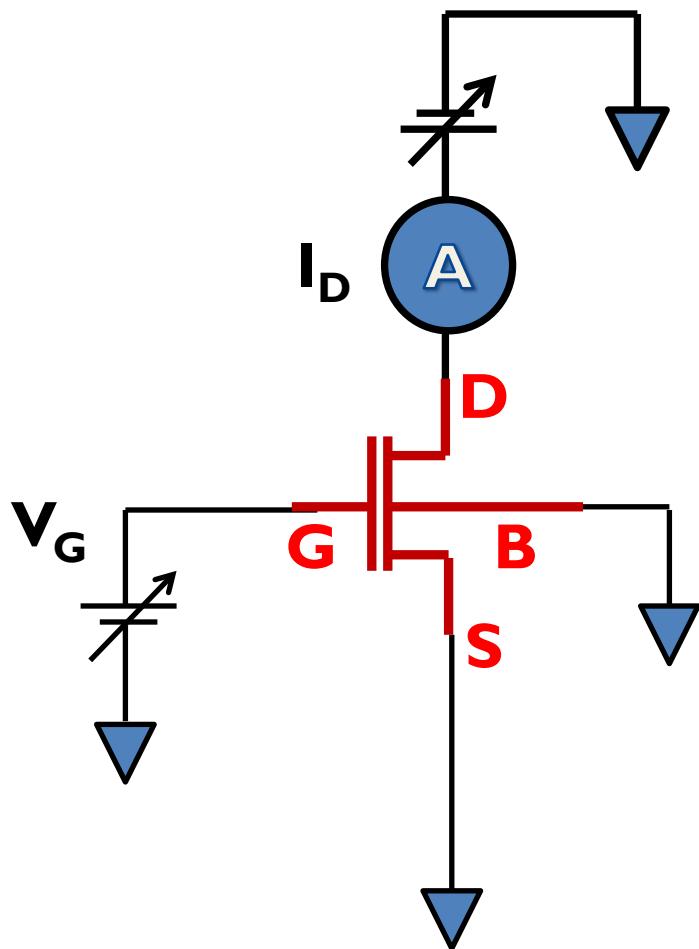
Taking snapshots sequentially...



Outline

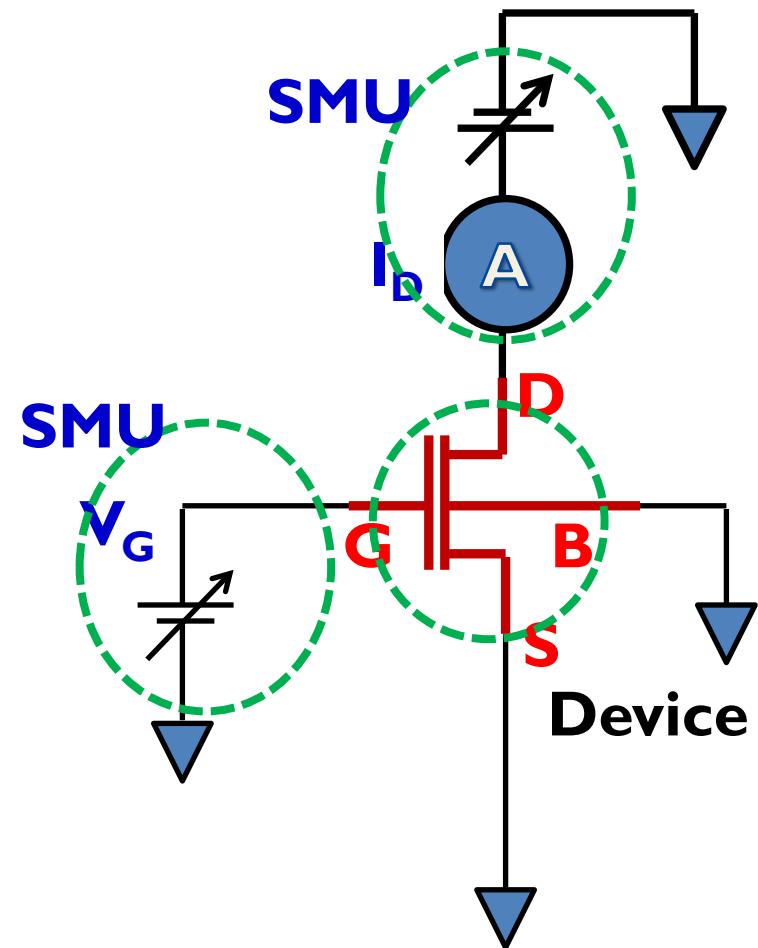
- I. Different reliability measurements
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Circuit Schematic



Measuring I_d - V_g as a function of time, for a certain stress condition

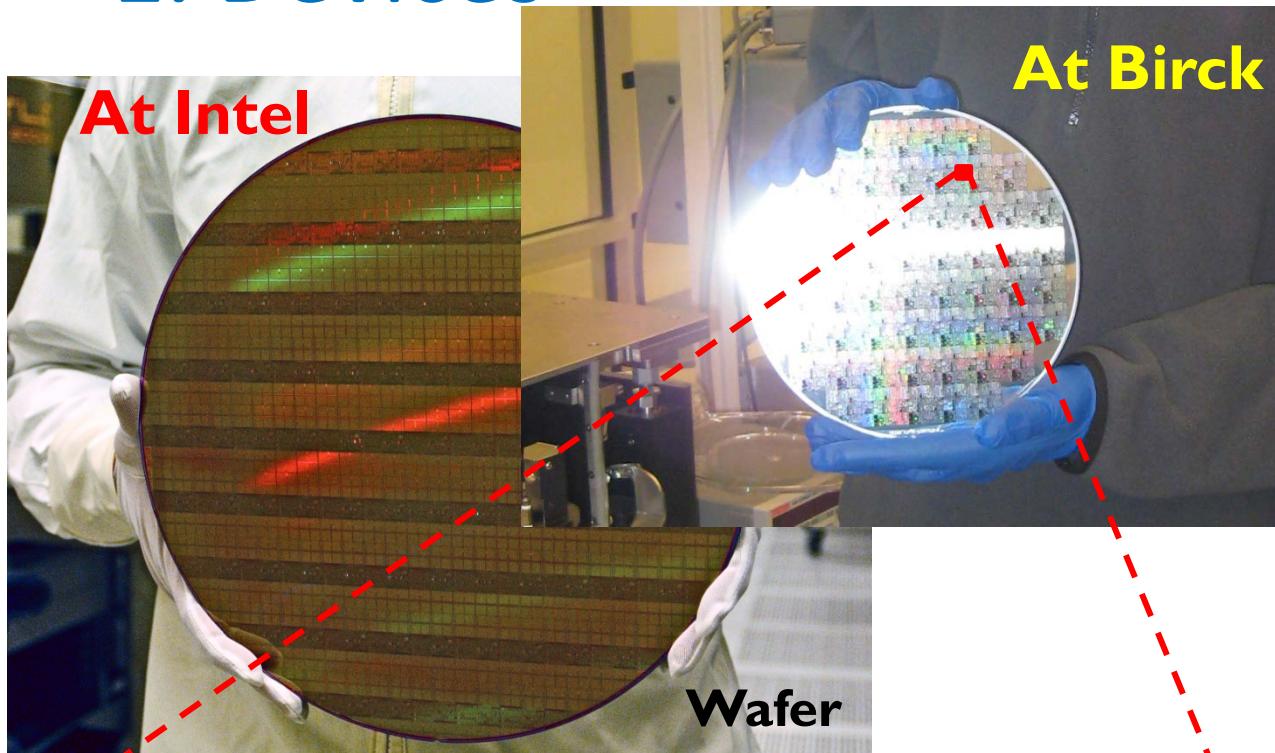
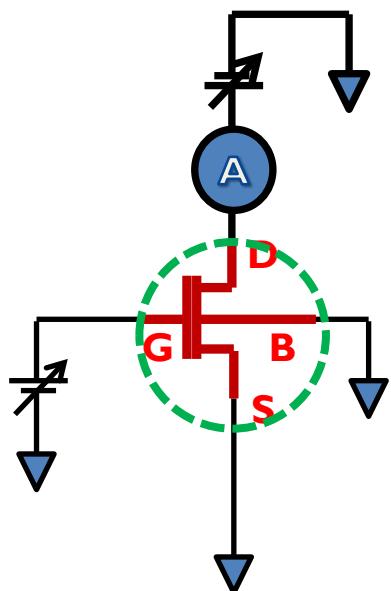
Different Components



1. Device
2. Probe station
3. (a) Voltage/Current **S**ource **U**nit
(Power Supply)
(b) Voltage/Current **M**easure **U**nit
(Multi-meter)

Integrated version:
Source **Measure **U**nit**

1. Devices



DUT	Width	Length	S	D	G
1	10	0.12	1	2	3
2	10	1	22	23	21
3	10	0.13	4	5	6
4	10	0.25	19	20	18
5	10	0.14	7	8	9
6	10	0.17	15	16	14
7	10	0.15	10	11	12

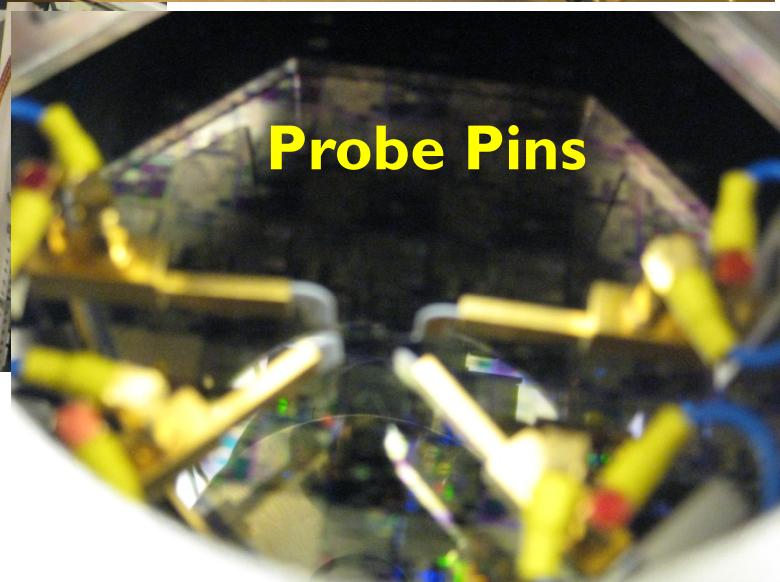
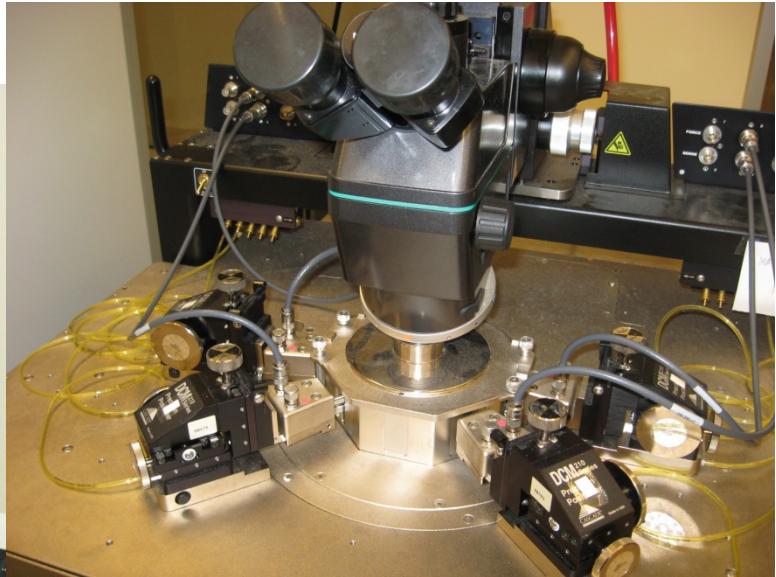
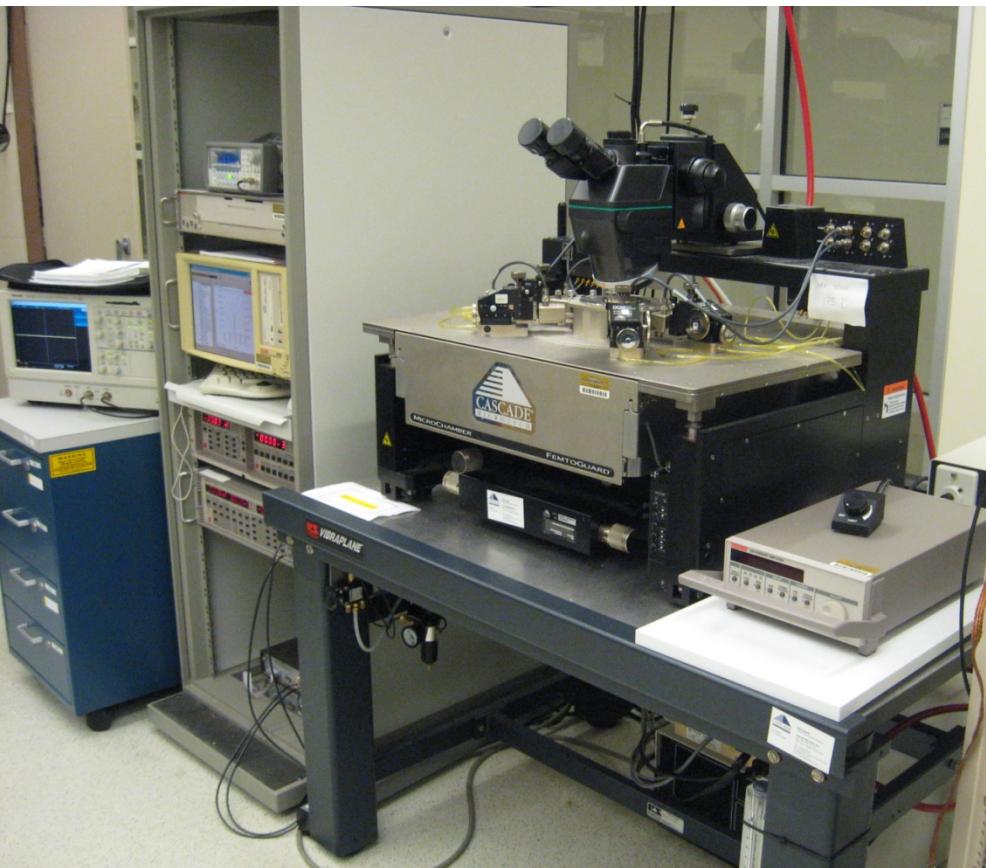
2. A modern Probe Station



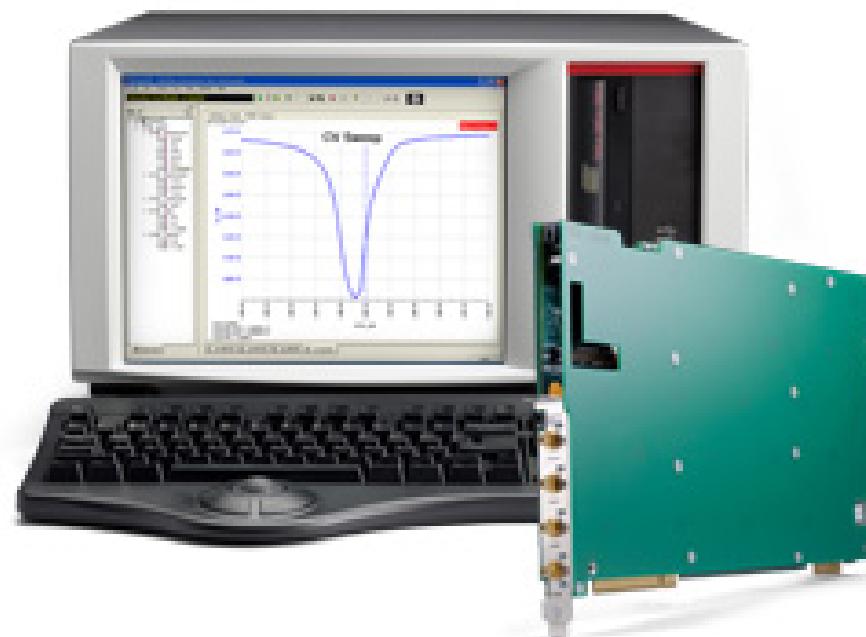
Noise, leakage and vibration isolation
Temperature controller...
Automatic, remote operation ...



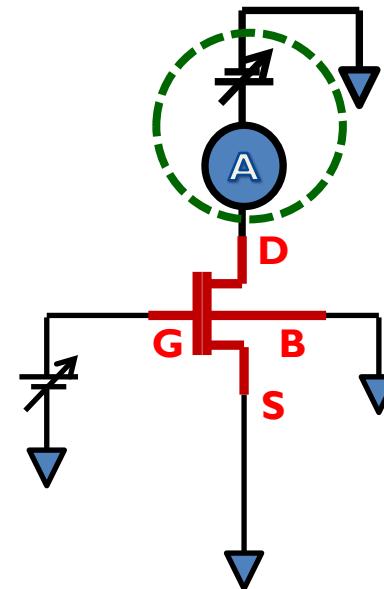
Probe Station: a closer look



3. Source-Measure Unit (SMU)

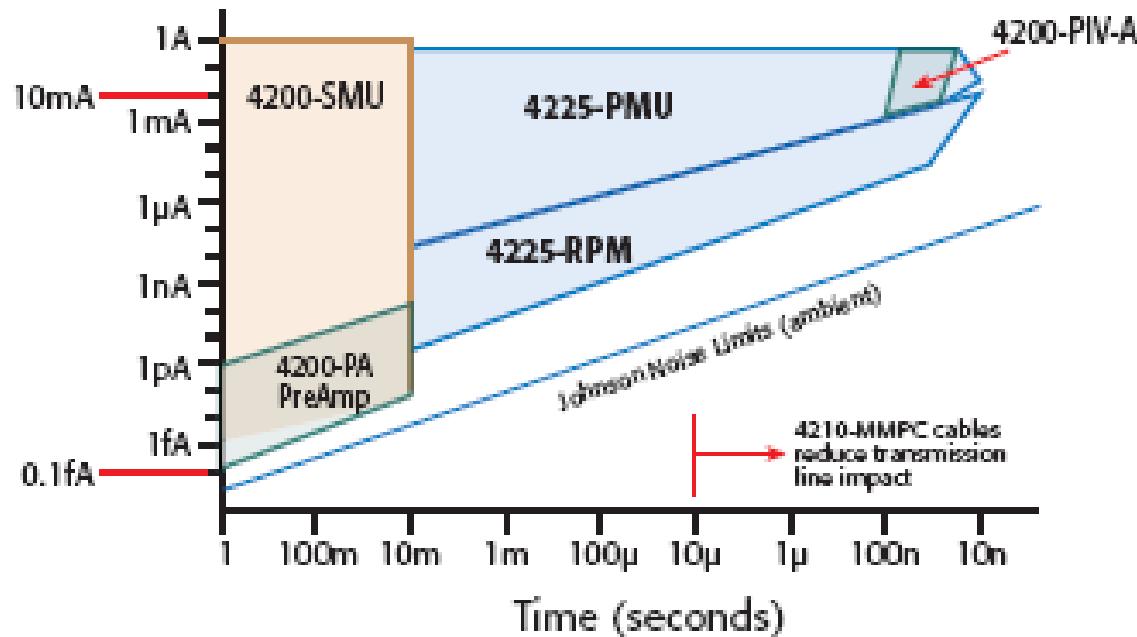


Standard SMU
Precision SMU (Better resolution)



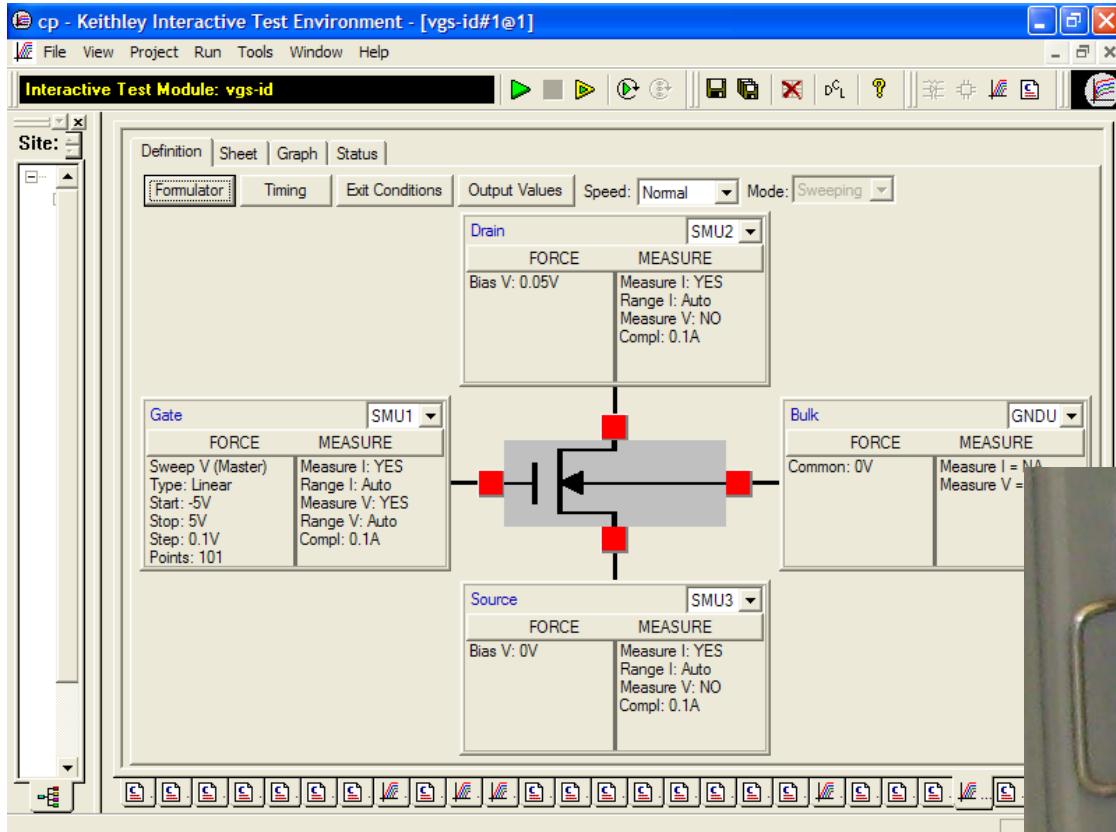
Noise and Resolution

Current Measurements vs. Time Comparison of Various Keithley DC and Pulsed I-V Instruments



The accuracy depends on speed of the measurement

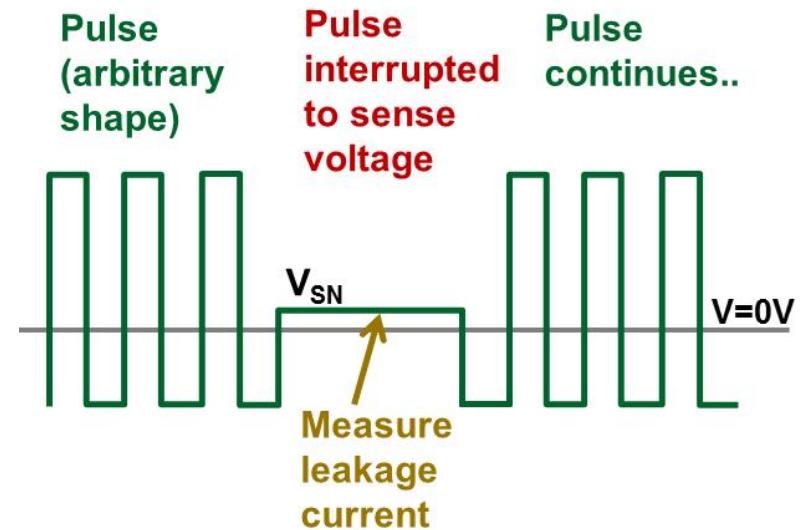
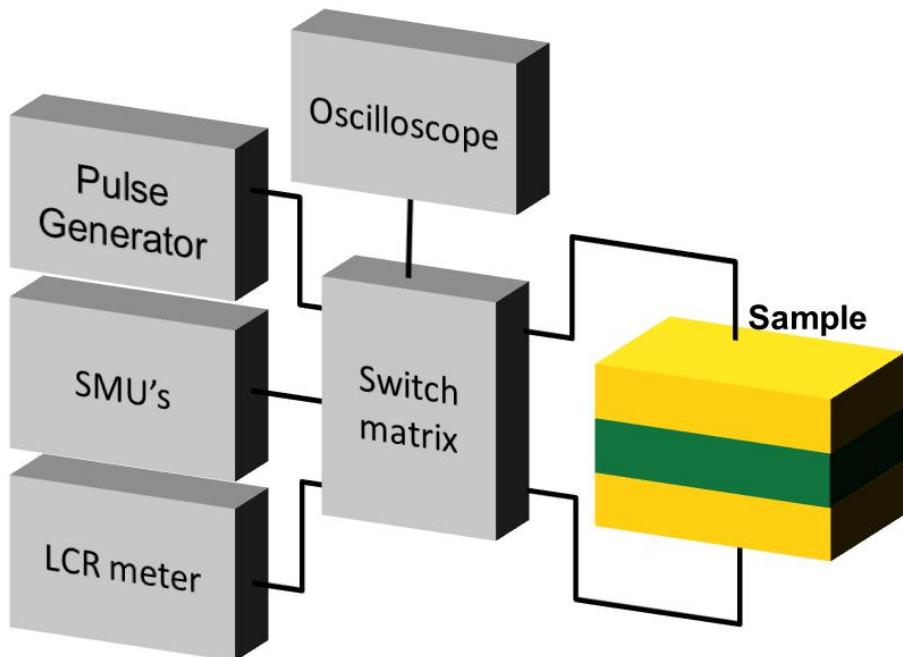
Running standard measurement



Standard program can be used for common measurements



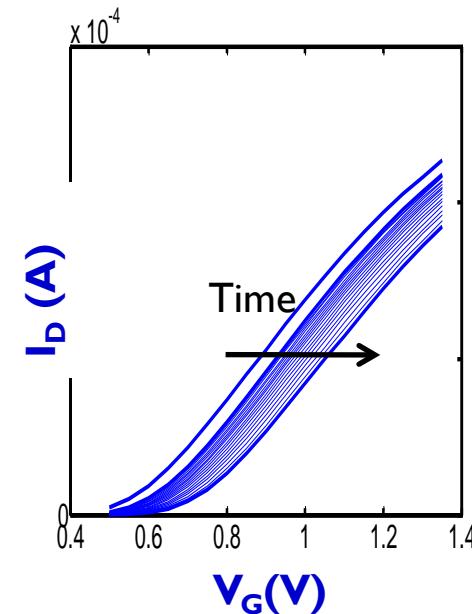
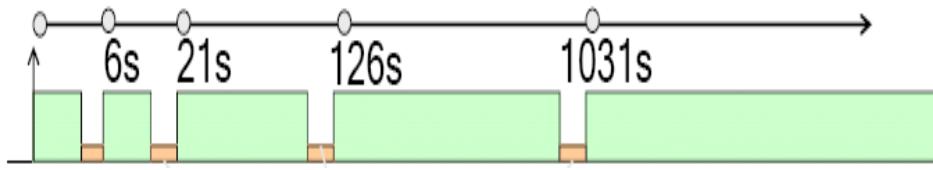
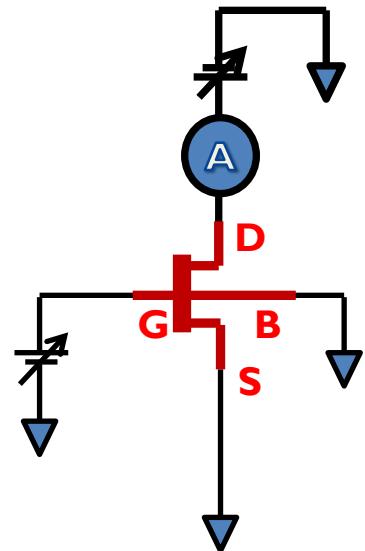
A complex measurement setup



Outline

- I. Different reliability measurements
2. Measurement setup
- 3. Example Codes**
4. Data analysis
5. Conclusion

1. MSM (I_D - V_G)

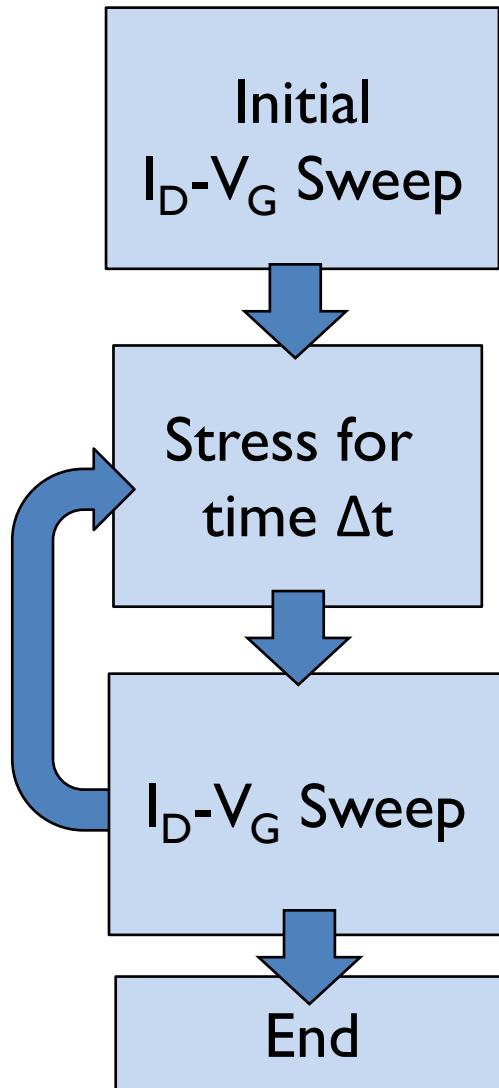


Setup

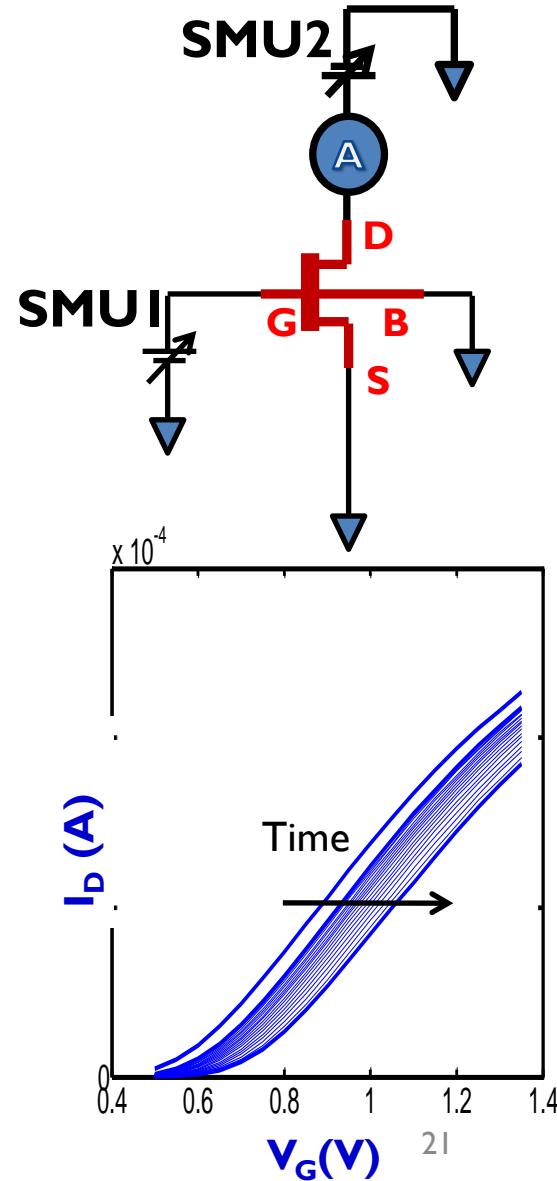
Measurement Sequence

Output

Measurement Flow Chart

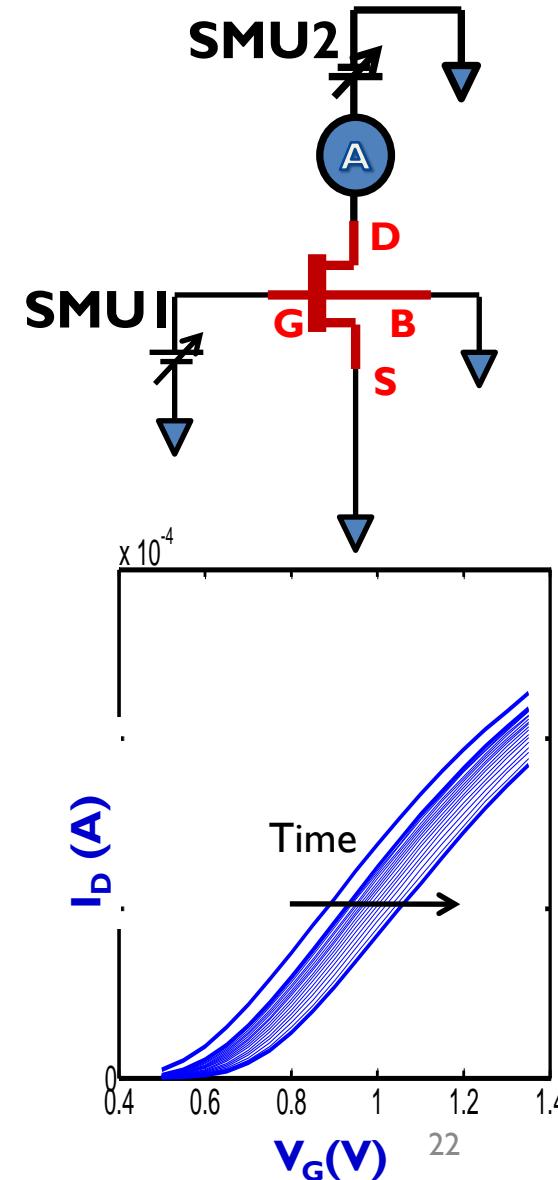


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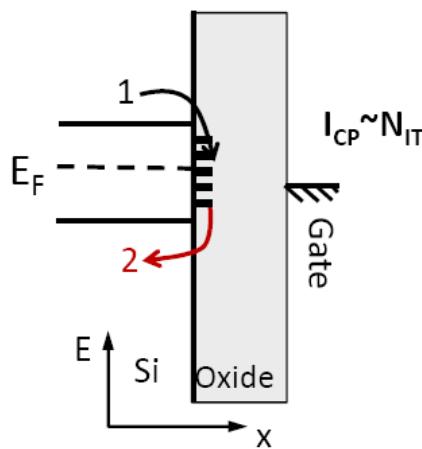
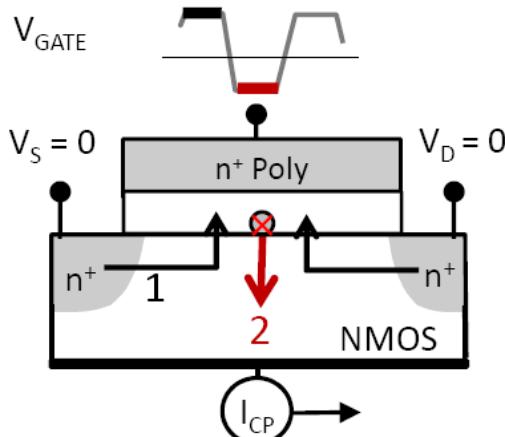


Measurement Code: MSM (I_D - V_G)

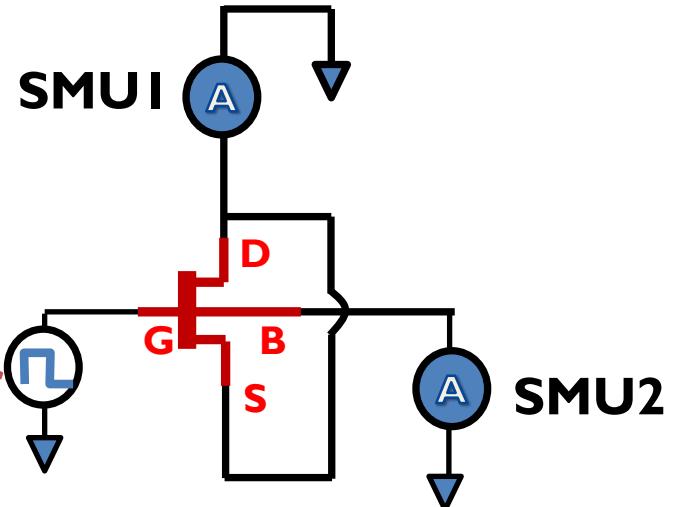
```
#include "keithley.h"
...
//-----
// 1. Settings
    devint();
    limiti(SMU1, 1e-1); limity(SMU1, 10);
// 2. Connect pins to SMUs, GND,..
    conpin(SMU1, gate_pin, 0);    conpin(SMU2, drain_pin, 0);
//-----
// 3. Apply stress
    forcev(SMU1, Vg_stress); forcev(SMU2, 0);
    delay(t); devclr();
//-----
//4. Measure Id-Vg
// Apply drain Voltage
    forcev(SMU2, V_drain);
    for (ct=1; ct<Vg_length; ct++)
    {
        // Apply Gate Voltage
        forcev(SMU1, V_gate(ct));
        // Measure Drain Current
        measi(SMU2, &i_meas(ct));
    }
//-----
```



Charge pumping (CP)



Function
Generator



Circuit Schematic

Measurement Code (CP)

```
#include "keithley.h"
```

```
... ...
```

// 1. Settings

```
devint(); limiti(SMUI, 1e-1); limity(SMUI, 10);
sprintf(cmd, "*RST\n"); fcnstat = kibsnd( fg, -1, GPIBTIMO, strlen(cmd), cmd);
....
```

// 2. Connect pins to SMUs, GND, Pulse Generator

```
conpin(SMUI, drain_pin, source_pin, 0); conpin(SMU2, bulk_pin, 0);
conpin(GPI_fg, gate_pin, 0);
//-----
```

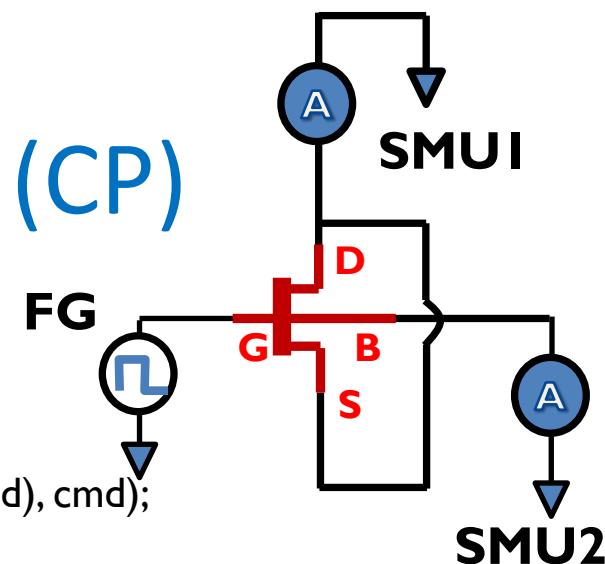
// 3. Apply Voltage

```
forcev(SMU1, 0); forcev(SMU2, 0);
```

// Pulse Generator

```
sprintf(cmd, ":VOLT %fV\n", ampl);
sprintf(cmd, ":VOLT:OFFS %fV\n", offset);
sprintf(cmd, ":FREQ %f\n", freq_CP);
sprintf(cmd, ":FUNC:PULS:DCYC %f\n", 50);
sprintf(cmd, ":FUNC:PULS:TRAN %le\n", 1e-7);
sprintf(cmd, ":OUTP ON\n");
```

```
fcnstat = kibsnd(fg, -1, GPIBTIMO, strlen(cmd), cmd);
```

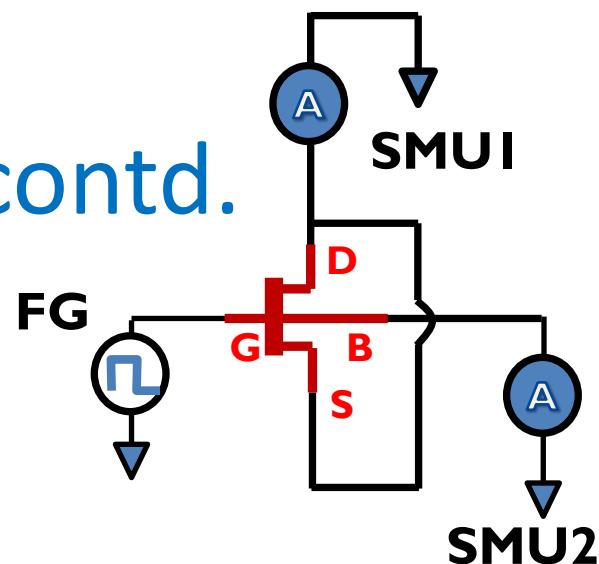


Measurement Code (CP)...contd.

```
//-----
```

//4. Measure CP current

```
measi(SMUI, &icp1);  
measi(SMU2, &icp2);
```



```
//-----
```

//5. Reset Instruments

```
sprintf(cmd, ":OUTP OFF\n");    fcnstat = kibsnd(fg, -1, GPIBTIMO, strlen(cmd), cmd);  
clrcon();
```

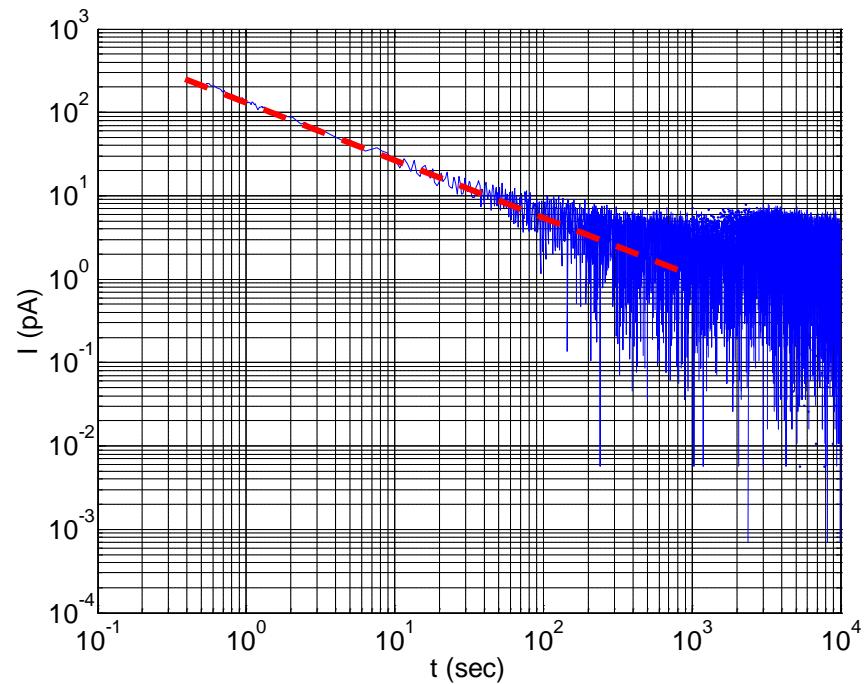
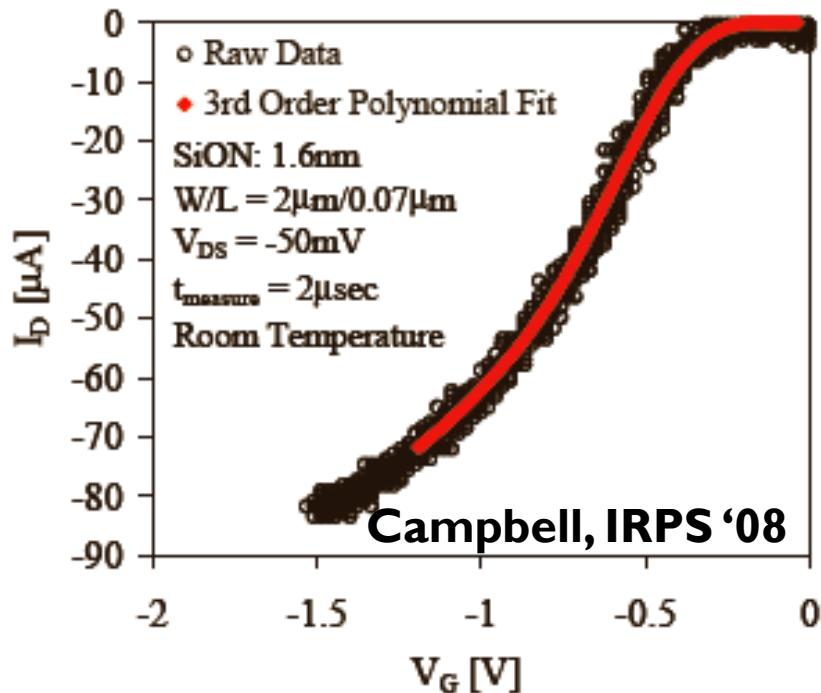
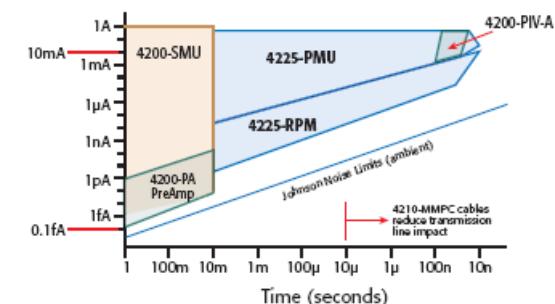
//6. Save data

```
fprintf(fp_out, "icp1= %e A, icp2= %e A", icp1, icp2);
```

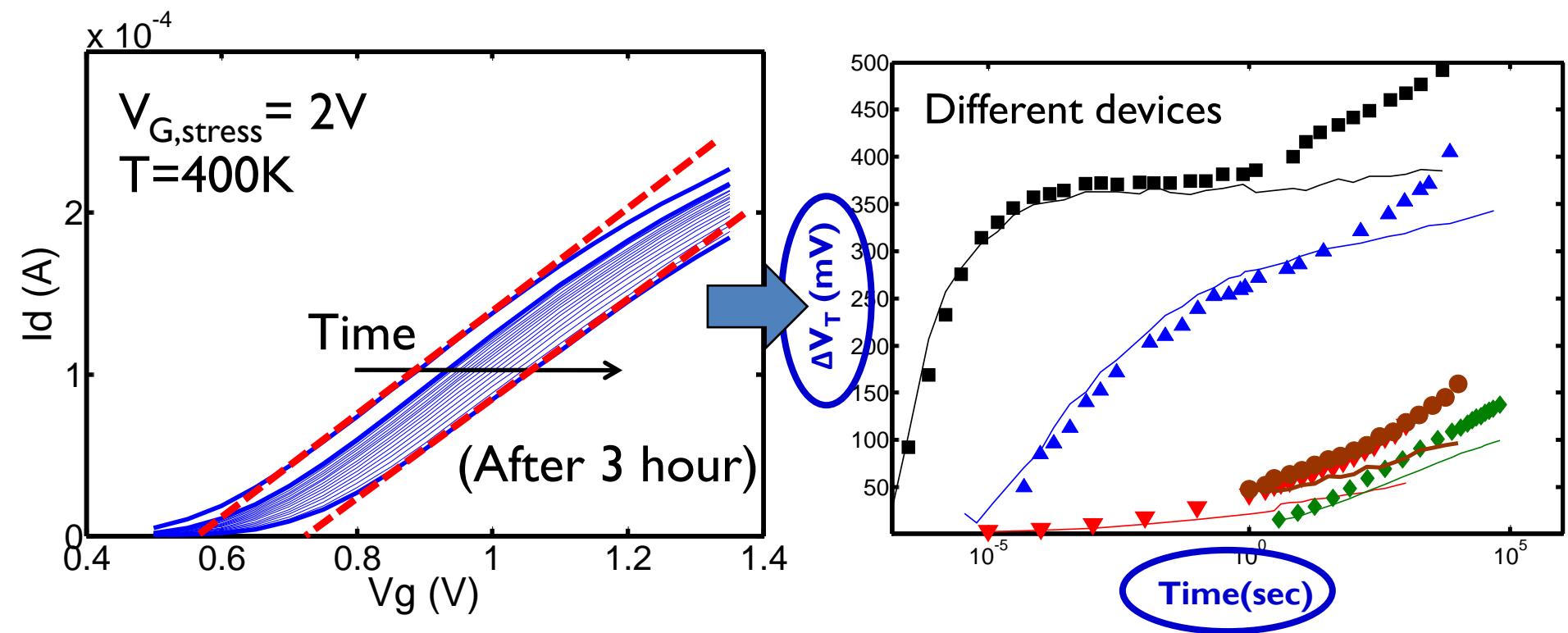
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Fast Measurement Issue: Noise



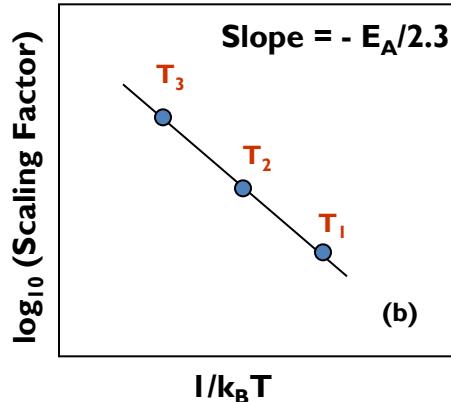
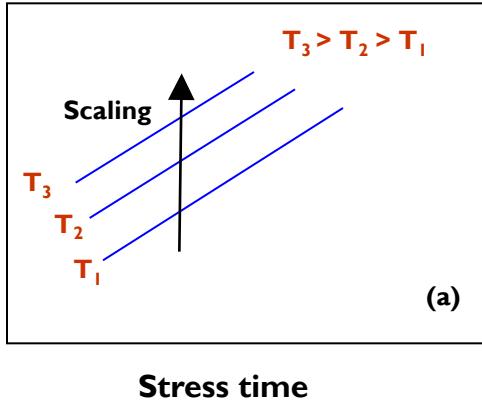
Extraction of V_T and ΔV_T



Maximum g_m ,other method..

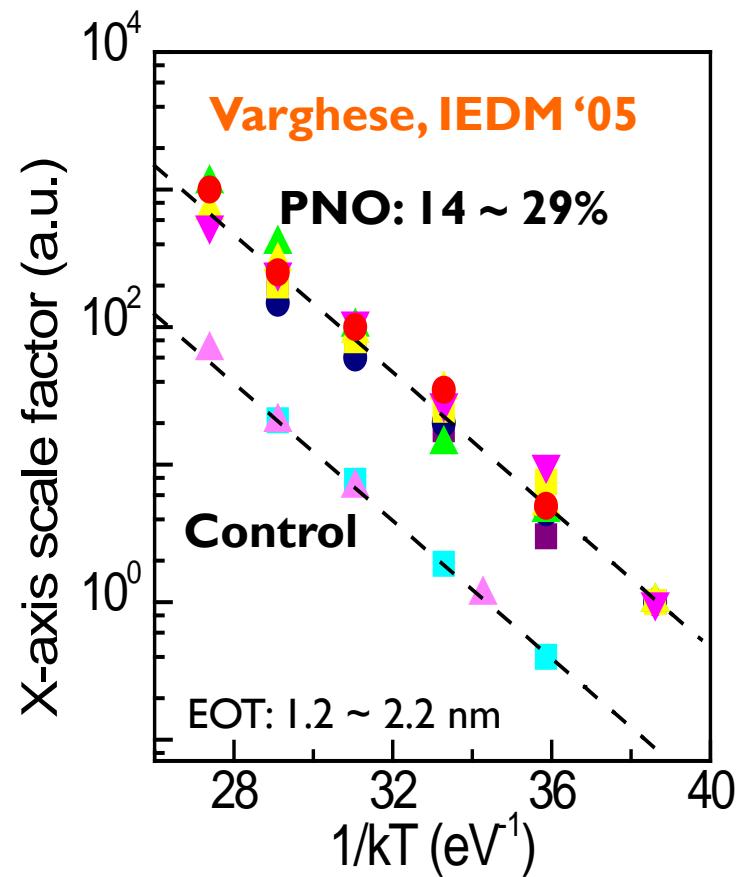
Temperature Activation

Degradation



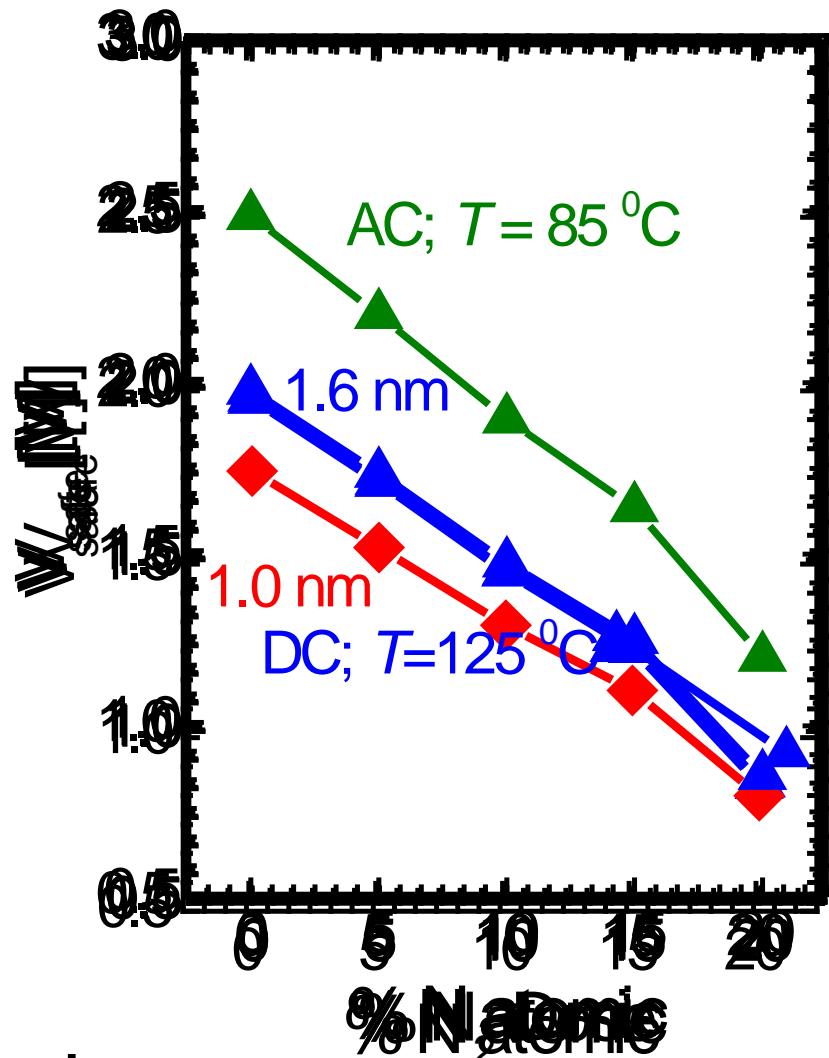
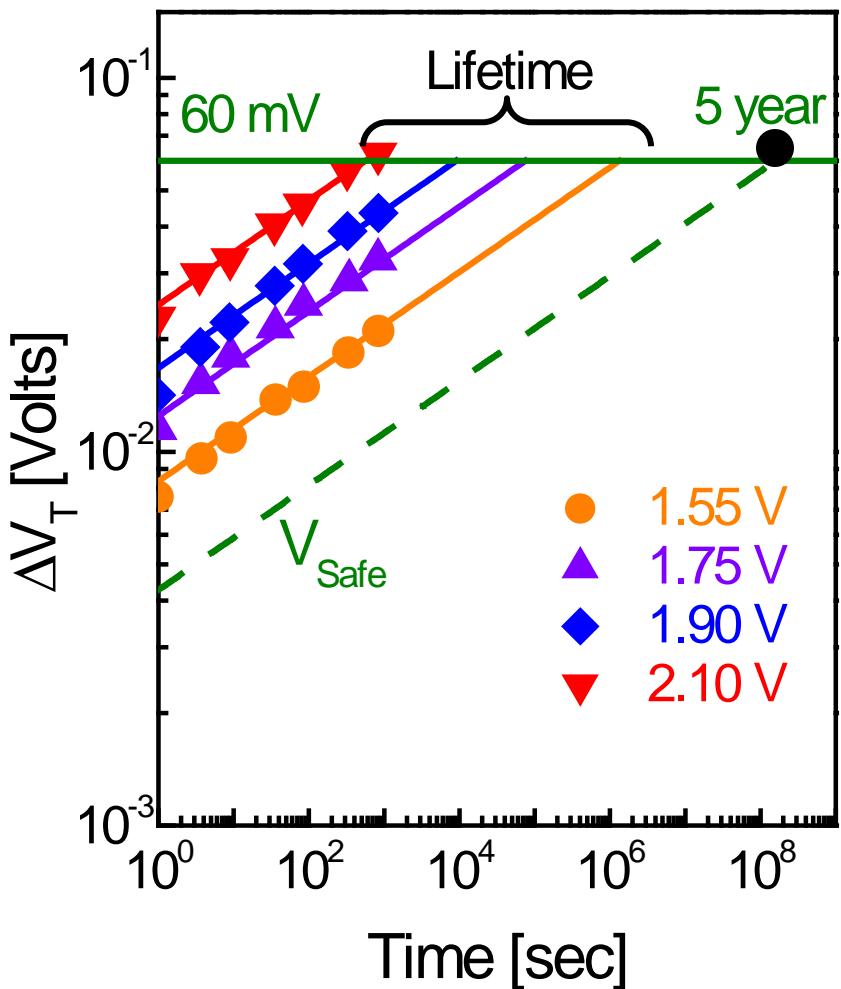
$$\Delta V_T \sim \exp\left(-\frac{E_A}{k_B T}\right)$$

- Temperature dependent data
 - a) Data scaled along X/Y-axis
Scaling factors: $S_1 = 1, S_2, S_3$
 - b) $\log_{10} S$ vs. $(1/kT)$ drawn
Slope = $-E_A/2.3$
- Wide range of temperature ($27^{\circ}\text{C} \sim 150^{\circ}\text{C}$)



$$E_A (\text{avg.}) \sim 0.58 \text{ eV}$$

NBTI Lifetime & Safe Condition



V_{safe} depends on
N₂ dose Temperature

DC/AC

Conclusions

We have answered the following questions:

- Why precision measurements are so important in reliability modeling,
- Characteristics of reliability measurements
- What are the different components for a measurement setup,
- How to perform $SMS-I_DV_G$ and Charge pumping measurements
- How to use the raw data to extract useful information